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 09/820072  
 03/28/01



Form PTO-1449 Department of Commerce Patent and Trademark Office  <b>INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION</b>  (Use several sheets if necessary)	Docket No. <b>PAT004</b>	Serial No. <b>Unassigned</b>
	<b>Applicants</b> <b>Wen-Yen Hwang</b>	
	Filing Date <b>Herewith</b>	Group Art Unit <b>Unassigned</b>

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TN	5,285,086	02/08/94	Fitzgerald, Jr.			
	5,294,808	03/15/94	Lo			
	5,513,204	04/30/96	Jayaraman			
	5,719,894	02/17/98	Jewell <i>et al.</i>			
	5,754,578	5/19/98	Jayaraman			
	5,914,976	6/22/99	Jayaraman <i>et al.</i>			
	5,981,400	11/09/99	Lo			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES   NO

## OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

TN	Matthews, J. W. and Blakeslee, A. E., "Defects in Epitaxial Multilayers," <i>Journal of Crystal Growth</i> 27, (1974), pp. 118-125.
	Parillaud <i>et al.</i> , "High Quality InP on Si by Conformal Growth," <i>Appl. Phys. Lett.</i> 68, (1996), p. 2654.
	Lo, Yu-Hwa, "Long Wavelength Vertical Cavity Surface Emitting Lasers," <i>Hot Topic</i> , February 1995, p. 20-21.

EXAMINER	<b>JOSEPH NGUYEN</b>	DATE CONSIDERED	<b>10/10/02</b>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.



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JN	Qian <i>et al.</i> , "1.3μm Vertical-Cavity Surface-Emitting Lasers with Double-Bonded GaAs-AlAs Bragg Mirrors," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 1, January 1997, pp. 8-10.					
	Uchiyam <i>et al.</i> , "Continuous-Wave Operation up to 36°C of 1.3μm GaInAsP-InP Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 2, February 1997, pp. 141-142.					
	Dudley, <i>et al.</i> , "Low Threshold, Wafer Fused Long Wavelength Vertical Cavity Lasers," <i>Appl. Phys. Lett.</i> 64 (12), March 1994, pp. 1463-1465.					
	Xiong, Yanyan and Lo, Yu-Hwa, "Current Spreading and Carrier Diffusion in Long-Wavelength Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 9, September 1998, pp. 1202-1204.					
	Salet <i>et al.</i> , "Undercut Ridge Structures: A Novel Approach to 1.3/1.55μm Vertical-Cavity Lasers Designed for Continuous-Wave Operation," <i>IEEE Proc.-Optoelectron.</i> , Vol. 145, No. 2, April 1998, pp. 125-131.					
	Salet <i>et al.</i> , "Room-Temperature Pulsed Operation of 1.3μm Vertical-Cavity Lasers Including Bottom InGaAsP/InP Multilayer Bragg Mirrors," <i>Electronics Letters.</i> , Vol. 33, No. 24, November 1997, pp. 2048-2049.					
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JN	Salet <i>et al.</i> , "Gas-Source Molecular-Beam Epitaxy and Optical Characterisation of Highly-Reflective InGaAsP/InP Multilayer Bragg Mirrors for 1.3μm Vertical-Cavity Lasers," <i>Electronics Letters.</i> , Vol. 33, No. 13, June 1997, pp. 1145-1147.					
	Qian, <i>et al.</i> , "Submilliamp 1.3μm Vertical-Cavity Surface-Emitting Lasers With Threshold Current Density of <500A/cm <sup>2</sup> ," <i>Electronics Letters</i> , Vol. 33, No. 12, June 1997, pp. 1052-1054.					
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10/09/2007  
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